SEMICONDUCTOR

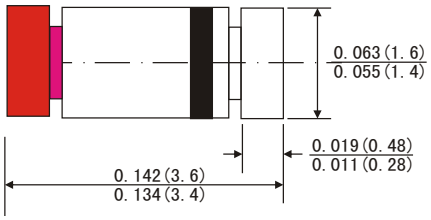
LL19

SMALL SIGNAL SCHOTTKY DIODES

FEATURES

- Metal-on-silicon junction
- Low turn-on voltage
- Ultrafast switching speed
- Primarily Intended for high level UHF/VHF detection and pulse applications with broad dynamic range
- The diode is also available in the DO-35 case with type designation BAT19,
- High temperature soldering guaranteed:260℃/10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

MiniMELF



Dimensions in inches and (millimeters)

MECHANICAL DATA

- *Case*: MiniMELF glass case(SOD-80)
- Polarity: Color band denotes cathode end
- *Weight*: Approx. 0.05 gram

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Peak Reverse Voltage	V_{RRM}	10	V
Forward Continuous Current	I_F	30	mA
Surge non repetitive Forward current $t_p \leqslant 1s$	I_{FSM}	2. 0	A
Storage temperature range	T_{STG}	-55 to+150	℃
Junction temperature	T_J	125	℃

ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Unis
Reverse breakover voltage at I_R=10μA	V_R	10			V V
Leakage current at V_R=5V	I_R			100	nA
Forward voltage drop at I_F=1mA Test pulse:$t_p \leqslant 300\mu s$ $\delta < 2\%$ I_F=20mA	V_F V_F			0.40 1.0	V V
Junction Capacitance at V_R=0V ,f=1GHz	C_J			1.2	pF
Thermal resistance	$R_{\theta JA}$			400	K/W

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RATINGS AND CHARACTERISTICS CURVES LL19

Figure 1. Forward current versus forward voltage at low level(typical values)

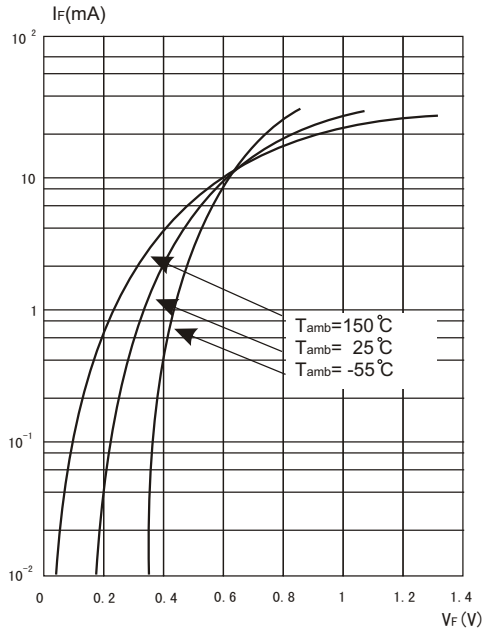


Figure 2. Capacitance CJ versus reverse applied voltage VR (typical values)

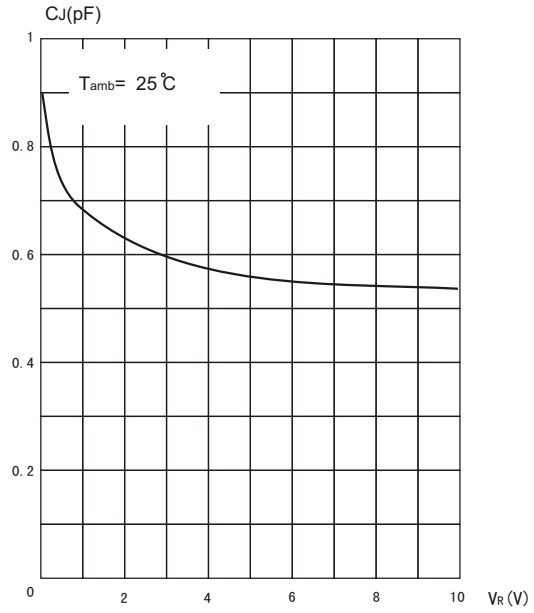


Figure 3.Reverse current versus ambient temperatures

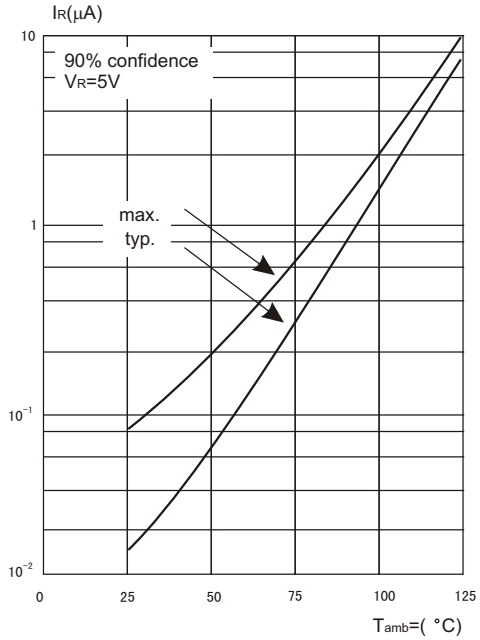
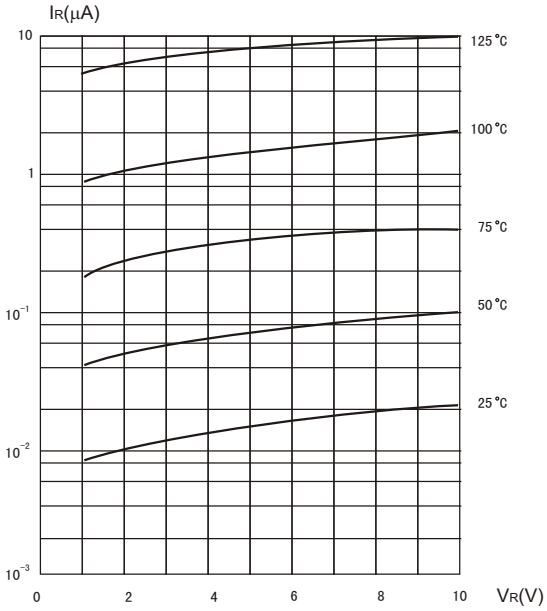


Figure 4.Reverse current versus continuous Reverse voltage(typical values)



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